Rd50 full detector system mask design

G. Casse, P. Turner

Controlling the edge current

Using miniature detectors for flexibility to use

Reverse current in miniature detector or diodes implemented as test structures on Glast or Atlas detector masks. Traditional G.R.





The detectors are cut to reduce the distance from the edge to the active area.





Proposed geometries to control the edge field. Trench etched outside the guardrings.

More extreme solutions with without or backside guard-rings.



Miniature detectors with about 100-120 strips, suitable for bonding to available 40MHz analogue electronics (e.g. SCT128A – 128 channels). The number of strips can be variable between detector types in order to keep straight cutting lines on the wafer (for economy reasons). The choice of miniature detectors allows to put more devices on a single wafer and to reduce the parallel noise contribution (short strips).

The standard microstrip structure (SMS) here proposed is 80 µm strip pitch and 20µm width, with 125 strips/cm.

We propose the following detector types:

- Type 1: SMS with 100 µm distance of the sensitive area to the cutting edge (d), 1 guard ring (GR).
- Type 2: SMS with $d = 200 \ \mu m$ and 4 GRs.
- Type 3: SMS with $d = 300 \ \mu m$ and 6 GRs
- Type 4: SMS with $d = 400 \ \mu m$ and 8 GRs

And the following trenched structures

- Type 5: SMS with $d = 100 \ \mu m$ and no GRs
- Type 6: SMS with $d = 200 \ \mu m$ and 3 GRs
- Type 7: SMS with $d = 300 \ \mu m$ and 6 GRs
- Type 8: SMS with $d = 400 \ \mu m$ and 8 GRs







Type 2









Type 8



 $32 \sim 1X1$ cm-2 miniature detectors can be allocated on a 4" wafer, allowing 4 detectors per each type. For cost reduction, it would be appropriate to produce a single mask set and several copies to distribute to the interested manufacturers. To realise this, a common set of alignment marks should be agreed with the manufacturers.